Silicon NPN Power Transistors 2SD1455

DESCRIPTION

- With TO-3PN package
- High voltage,high speed
- Built-in damper diode

APPLICATIONS

- For TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

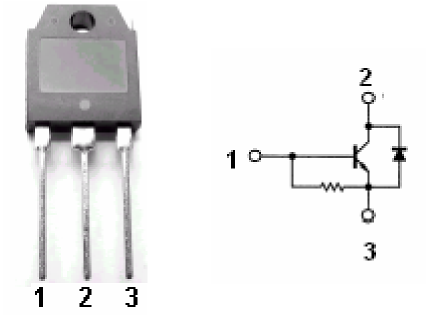

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		5	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-45~150	□

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=200mA; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4.5A; I_B=1.2A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4.5A; I_B=1.2A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1500V; I_E=0			0.5	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	6			
V_F	Diode forward voltage	I_F=5A			2.2	V

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PACKAGE OUTLINE

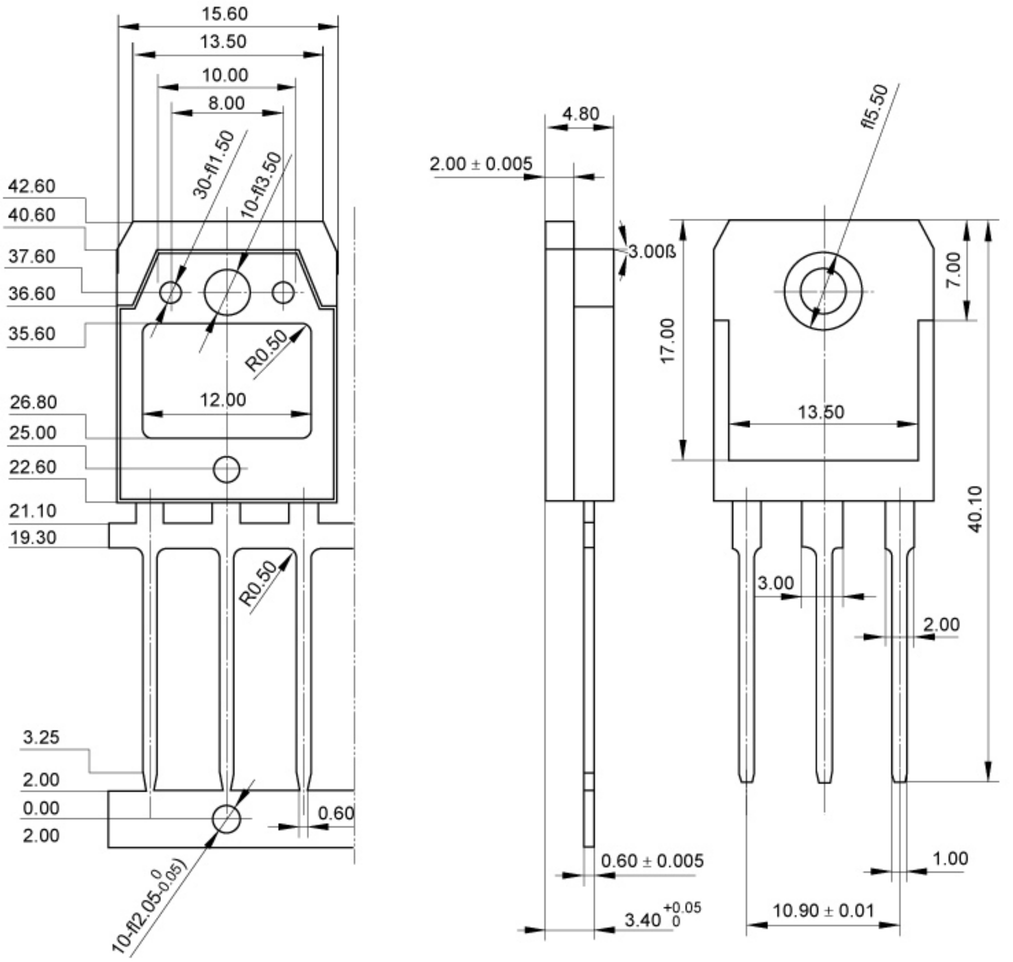

Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)